

**IN THE CLAIMS:**

Claim 1 (Original): A method of fabricating a liquid crystal display device,  
comprising:

forming a thin film transistor in a pixel region and a pad on an edge region of a  
first substrate;

depositing an organic passivation layer over the first substrate; and

removing the organic passivation layer in the edge region using a diffraction  
mask to expose a portion of the pad, wherein the diffraction mask has a slit portion  
including a plurality of slits having different widths.

Claim 2 (Original): The method of claim 1, wherein the organic passivation layer is  
formed of one of benzo cyclo butene (BCB) and photo-acryl.

Claim 3 (Currently Amended): The method of claim 1, wherein the removing the  
organic passivation comprises,

depositing a photoresist layer on the organic passivation layer in the edge  
region;

placing the diffraction mask having first and second light transmission regions  
over the photoresist layer for a light exposure, so that the first light transmission  
region transmits an amount of light greater than the second light transmission region;

developing the photoresist layer to completely remove the photoresist layer ~~corresponding to~~ of the second light transmission region and to ~~remain~~ retain the photoresist layer corresponding to of the first light transmission region;

etching the organic passivation layer to remove a part of the organic passivation layer corresponding to of the second light transmission region;

removing the retained photoresist layer corresponding to the first light transmission region; and

etching the organic passivation layer to remove ~~a remaining~~ the organic passivation layer in the first and second light transmission regions.

Claim 4 (Original): The method of claim 3, wherein the diffraction mask of the second transmission region has a slit width greater than that of the first transmission region.

Claim 5 (Original): The method of claim 3, wherein the diffraction mask of the second light transmission region has a plurality of slits.

Claim 6 (Original): The method of claim 1, wherein the forming a thin film transistor comprises,

- forming a gate electrode on the first substrate;
- depositing a gate insulating layer over the first substrate;
- forming a semiconductor layer on the gate insulating layer; and
- forming a source electrode and a drain electrode on the semiconductor layer.

Claim 7 (Original): The method of claim 1, further comprising forming a metal layer on the exposed portion of the pad.

Claim 8 (Original): The method of claim 7, wherein the metal layer is formed of one of indium tin oxide (ITO) and indium zinc oxide (IZO).

Claim 9 (Original): The method of claim 1, further comprising:

- forming a black matrix and a color filter layer on a second substrate;
- forming a sealant on the edge region of the first substrate and attaching the first and second substrates to each other; and
- forming a liquid crystal layer between the first and second substrates.

Claim 10 (Original): A method of fabricating a liquid crystal display device,

comprising:

forming a thin film transistor in a pixel region and a pad on an edge region of a first substrate;

depositing an organic passivation layer over the first substrate;

depositing a photoresist layer on the organic passivation layer in the edge region;

placing the diffraction mask having first and second light transmission regions over the photoresist layer for a light exposure, so that the first light transmission region transmits an amount of light greater than the second light transmission region;

developing the photoresist layer to completely remove the photoresist layer of the second light transmission region and to remain the photoresist layer of the first light transmission region;

etching the organic passivation layer to remove a part of the organic passivation layer of the second light transmission region;

removing the photoresist layer; and

etching the organic passivation layer to remove a remaining organic passivation layer.

Claim 11 (Original): The method of claim 10, wherein the organic passivation layer is formed of one of benzo cyclo butene (BCB) and photo-acryl.

Claim 12 (Original): The method of claim 10, wherein the diffraction mask of the second transmission region has a slit width greater than that of the first transmission region.

Claim 13 (Original): The method of claim 10, wherein the diffraction mask of the second light transmission region has a plurality of slits.

Claim 14 (Original): The method of claim 10, wherein the forming a thin film transistor comprises,

- forming a gate electrode on the first substrate;
- depositing a gate insulating layer over the first substrate;
- forming a semiconductor layer on the gate insulating layer; and
- forming a source electrode and a drain electrode on the semiconductor layer.

Claim 15 (Original): The method of claim 10, further comprising forming a metal layer on the exposed portion of the pad.

Claim 16 (Original): The method of claim 15, wherein the metal layer is formed of one of indium tin oxide (ITO) and indium zinc oxide (IZO).

Claim 17 (Original): The method of claim 10, further comprising:

forming a black matrix and a color filter layer on a second substrate;

forming a sealant on the edge region of the first substrate and attaching the first  
and second substrates to each other; and

forming a liquid crystal layer between the first and second substrates.